GSDSRB521N6-30F

Schottky Diode

Product Description

Schottky Barrier Diode 30V and 100mA

Features

- Low Forward Voltage

Mechanical Data

- DFN0603-2L Package
- RoHS Compliant and Halogen Free

Package and Pin Assignment

DFN0603-2L		Equivalent Circuit	
			
Pin	**Description**	**Pin**	**Description**
1	Anode	2	Cathode

Ordering and Marking Information

GS P/N	Package	Marking	Quantity / Reel
GSDSRB521N6-30F	DFN0603-2L	F	15,000 PCS

GSDSRB521N6-30F

- **Product Code:** GSDSRB521
- **Package Code:** **N6** for DFN0603-2L
- **Voltage Code:** **30** is Reverse Voltage 30V
- **Green Level:** **F** for RoHS Compliant and Halogen Free

Marking Information



- **Product Code:** **F**
- Band denotes Cathode Pin

Absolute Maximum Ratings (T_A=25ºC unless otherwise specified)

Symbol	Parameter	Value	Unit
V_R	Reverse Voltage	30	V
$I_{F(AV)}$	Average Forward Current	100	mA
I_{FSM}	Non-Repetitive Peak Forward Current (8.3ms Single Half Sin-Wave)	500	mA
P_D	Power Dissipation	100	mW
T_J	Junction Temperature	125	ºC
T_{STG}	Storage Temperature Range	-55 to +125	ºC

Electrical Characteristics (T_A=25ºC unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_R	Reverse Voltage	I_R=50μA	30			V
I_R	Reverse Current	V_R=30V			50	μA
V_F	Forward Voltage	I_F=10mA			0.38	V
		I_F=100mA		0.46	0.53	

Typical Characteristics (T_A=25℃ unless otherwise specified)

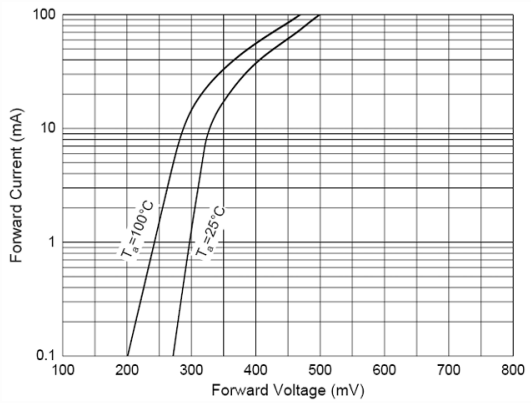


FIG.1 Forward Characteristics

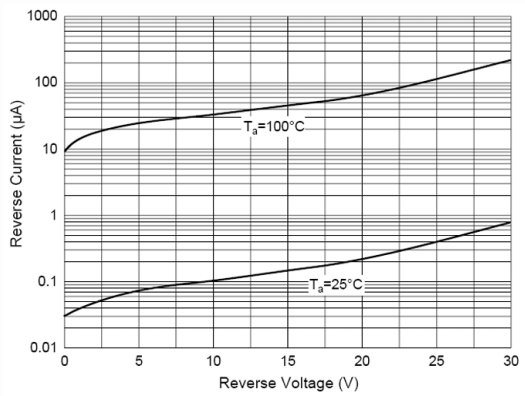


FIG.2 Reverse Characteristics

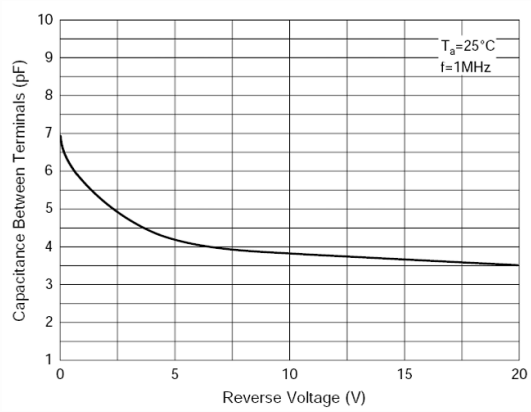


FIG.3 Capacitance Characteristics

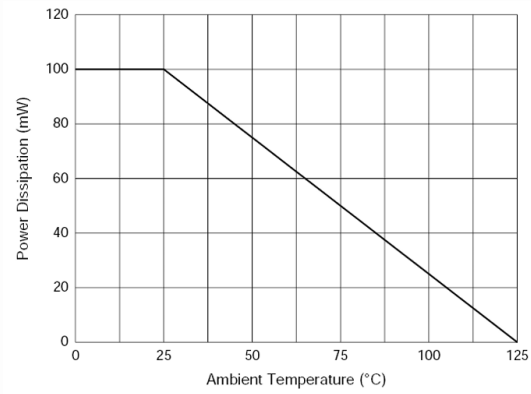
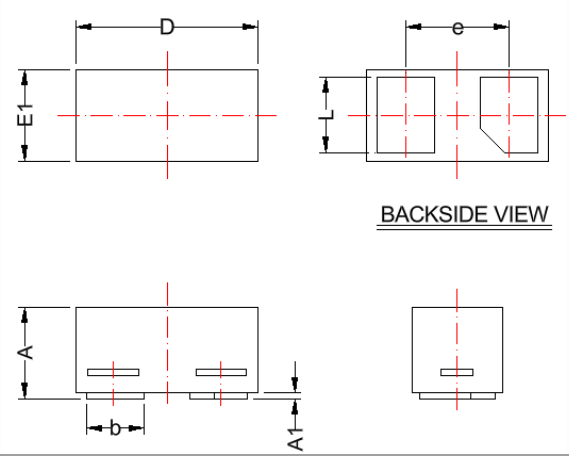


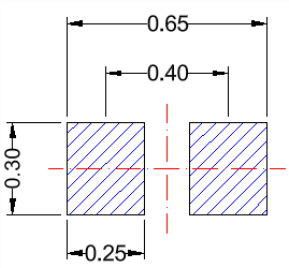
FIG.4 Power Derating Curve

DFN0603-2L

Package Dimension



Recommended Land Pattern



Unit:mm

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.28	0.32	0.011	0.013
A1	0.00	0.05	0.000	0.002
b	0.13	0.24	0.005	0.009
D	0.55	0.65	0.022	0.026
E1	0.25	0.35	0.010	0.014
e	0.35 BSC		0.014 BSC	
L	0.20	0.30	0.008	0.012

NOTE:

Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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